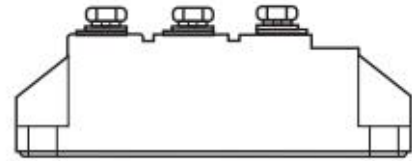
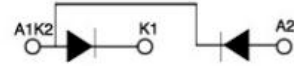


FEATURES

- Reduced RFI and EMI
- Reduced Snubbing
- Extensive Characterization of Recovery Parameters
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.



ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_R	Repetitive Peak Reverse Voltage	$t_p=10ms$	1400	V
$I_{F(AV)}$	Average Forward Current	Single phase, half-wave 180° condition, $T_c=100^\circ C$	60	A
I_{FSM}	Surge Forward Current	Single phase, half-wave, $V_R=0.6V_{RRM}$	86	A
I^2t	I^2t for fusing	Single phase, half-wave, $V_R=0.6V_{RRM}$	$8.6 \cdot 10^3$	A ² S
T_J	Junction Temperature		-40~150	°C
T_{stg}	Storage Temperature Range		-40~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.7	°C/W

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V _{FM}	Forward Voltage drop	I _F = 170A, T _J = 25°C	1.45	V
I _R	Instantaneous Reverse Current	V _R =V _{RRM} , T _J =150°C	8	mA

